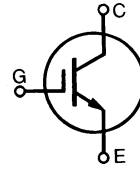


# HiPerFAST™ IGBT with Diode Lightspeed™ Series

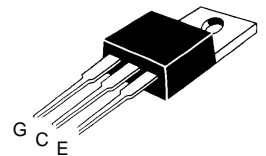
IXGA 7N60CD1  
IXGP 7N60CD1

$V_{CES} = 600 \text{ V}$   
 $I_{C25} = 14 \text{ A}$   
 $V_{CE(sat)typ} = 2.0 \text{ V}$   
 $t_{fi} = 45 \text{ ns}$

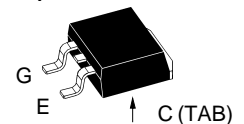


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	14	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	7	A
$I_{CM}$	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	30	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 22 \Omega$ Clamped inductive load, $L = 300 \mu\text{H}$	$I_{CM} = 14$ @ $0.8 V_{CES}$	A
$P_C$	$T_C = 25^\circ\text{C}$	54	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
$M_d$	Mounting torque, (TO-220)	M3 M3.5	0.45/4Nm/lb.in. 0.55/5Nm/lb.in.
<b>Weight</b>	TO-220		4 g
	TO-263		2 g

## TO-220AB (IXGP)



## TO-263 AA (IXGA)



G = Gate, C = Collector,  
E = Emitter, TAB = Collector

## Features

- International standard packages  
JEDEC TO-263 surface mountable and JEDEC TO-220 AB
- High frequency IGBT
- High current handling capability
- HiPerFAST™ HDMOS™ process
- MOS Gate turn-on  
- drive simplicity

## Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

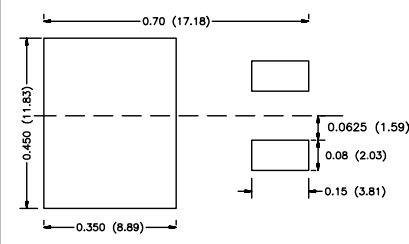
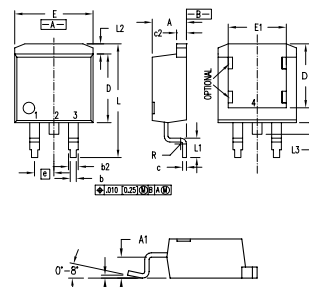
## Advantages

- High power density
- Suitable for surface mounting
- Very low switching losses for high frequency applications

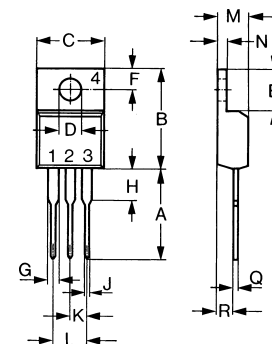
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	2.5		5.5 V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$		100 $\mu\text{A}$
		$T_J = 125^\circ\text{C}$		750 $\mu\text{A}$
$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$	2.0	2.5	V

Symbol	Test Conditions	Characteristic Values			
		(T <sub>J</sub> = 25°C, unless otherwise specified)			
		min.	typ.	max.	
<b>g<sub>fs</sub></b>	I <sub>C</sub> = I <sub>C90</sub> ; V <sub>CE</sub> = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	3	7	S	
<b>C<sub>ies</sub></b>	V <sub>CE</sub> = 25 V, V <sub>GE</sub> = 0 V, f = 1 MHz		500	pF	
<b>C<sub>oes</sub></b>			50	pF	
<b>C<sub>res</sub></b>			17	pF	
<b>Q<sub>g</sub></b>	I <sub>C</sub> = I <sub>C90</sub> ; V <sub>GE</sub> = 15 V, V <sub>CE</sub> = 0.5 V <sub>CES</sub>		25	nC	
<b>Q<sub>ge</sub></b>			15	nC	
<b>Q<sub>gc</sub></b>			10	nC	
<b>t<sub>d(on)</sub></b>	<b>Inductive load, T<sub>J</sub> = 25°C</b> I <sub>C</sub> = I <sub>C90</sub> ; V <sub>GE</sub> = 15 V, L = 300 μH V <sub>CE</sub> = 0.8 • V <sub>CES</sub> , R <sub>G</sub> = R <sub>off</sub> = 18 Ω Remarks: Switching times may increase for V <sub>CE</sub> (Clamp) > 0.8 • V <sub>CES</sub> , higher T <sub>J</sub> or increased R <sub>G</sub>		10	ns	
<b>t<sub>ri</sub></b>			10	ns	
<b>t<sub>d(off)</sub></b>			65	130	ns
<b>t<sub>fi</sub></b>			45	110	ns
<b>E<sub>off</sub></b>			0.12	0.25	mJ
<b>t<sub>d(on)</sub></b>	<b>Inductive load, T<sub>J</sub> = 125°C</b> I <sub>C</sub> = I <sub>C90</sub> ; V <sub>GE</sub> = 15 V, L = 300 μH V <sub>CE</sub> = 0.8 • V <sub>CES</sub> , R <sub>G</sub> = R <sub>off</sub> = 18 Ω Remarks: Switching times may increase for V <sub>CE</sub> (Clamp) > 0.8 • V <sub>CES</sub> , higher T <sub>J</sub> or increased R <sub>G</sub>		10	ns	
<b>t<sub>ri</sub></b>			15	ns	
<b>E<sub>on</sub></b>			0.15	mJ	
<b>t<sub>d(off)</sub></b>			120	ns	
<b>t<sub>fi</sub></b>			85	ns	
<b>E<sub>off</sub></b>		0.22	mJ		
<b>R<sub>thJC</sub></b>	IGBT			2.3 K/W	
<b>R<sub>thCK</sub></b>			0.25	K/W	

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
<b>V<sub>F</sub></b>	I <sub>F</sub> = 10A; T <sub>VJ</sub> = 150°C T <sub>VJ</sub> = 25°C			1.96 V 2.95 V
<b>I<sub>RM</sub></b>	V <sub>R</sub> = 100 V; I <sub>F</sub> = 25A; -di <sub>F</sub> /dt = 100 A/μs L ≤ 0.05 μH; T <sub>VJ</sub> = 100°C		2	2.5 V
<b>t<sub>rr</sub></b>	I <sub>F</sub> = 1 A; -di/dt = 50 A/μs; V <sub>R</sub> = 30 V T <sub>J</sub> = 25°C		35	ns
<b>R<sub>thJC</sub></b>	Diode			1.6 K/W

**Min. Recommended Footprint**

**TO-263 AA (IXGA) Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

**TO-220 AB (IXGP) Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110